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Silylation-Driven Volatility Enhancement in Mononuclear Calcium, Magnesium, and Barium Complexes with Monomethyl or Silyl Ether and Bis(diketonate)

Chanwoo Park,[#] Seungjin Song,[#] Heenang Choi, Bo Keun Park, Ji Yeon Ryu, Youngkwon Kim, and Taek-Mo Chung^{*}



ABSTRACT: Magnesium, calcium, and barium heteroleptic complexes were synthesized by the substitution reaction of the bis(trimethylsilyl)amide of Mg(btsa)₂·DME, Ca(btsa)₂·DME, and Ba(btsa)₂·2DME with an ethereal group and hfac ligands (btsa = bis(trimethylsilyl)amide, DME = dimethoxyethane). The compounds Mg(dts)(hfac)₂ (1), Ca(dts)(hfac)₂ (2), Mg(dmts)(hfac)₂ (3), Ca(dmts)(hfac)₂ (4), and Ba(dmts)(hfac)₂ (5) were fabricated and analyzed using various techniques, including Fourier transform infrared spectroscopy, nuclear magnetic resonance spectroscopy, thermogravimetric analyses, and elemental analysis (dts = 2,2-dimethyl-3,6,9-trioxa-2-siladecane, dmts = 2,2-dimethyl-3,6,9,12-tetraoxa-2-silatridecane, hfac = hexafluoroacetylacetonate). The structures of complexes 2, 4, and 5 were confirmed using single-crystal X-ray crystallography; all complexes display monomeric structures. All compounds underwent trimethylsilylation of the coordinating ethereal alcohols (meeH and tmgeH) in the presence of HMDS as byproducts because of their increasing acidity originating from the electron-withdrawing hfac ligands. (meeH = 2-(2-methoxyethoxy)ethan-1-ol, tmgeH = tri(ethylene glycol) monoethyl ether, HMDS = hexamethyldisilazane).



INTRODUCTION

The group two metal compounds containing magnesium, calcium, strontium, and barium are used in various fields, such as magnetoresistive materials, ferroelectrics, piezoelectric materials for dynamic random access memory (DRAM), and as precursors for thin-film growth.^{1–10} Electroceramics containing strontium oxide or barium oxide and transition metal oxides, such as SrTiO₃, Ba_{1-x}Sr_xTiO₃, BaTiO₃, BaSrTiO₃, and Y-doped BaZrO₃, exhibit high permittivity, dielectric constants, and high proton conductivity. However, calcium oxide and magnesium oxide have been used as gate-capacitor dielectrics in metal-oxide-semiconductor field-effect transistors (MOSFETs) and high-electron-mobility transistors (HEMTs). Additionally, magnesium and calcium have been used as optical coating materials for metal fluorides (MgF₂ and CaF₂).^{11–19}

The fabrication of thin films containing group two metal oxides or metal fluorides is required for these applications. These metal compounds can be deposited using chemical vapor phase methods, such as metal—organic chemical vapor deposition (MOCVD) and atomic layer deposition (ALD), which require volatile and thermally stable precursors. The development of volatile group two metal compounds is often limited by the formation of oligomeric compounds, particularly strontium, and barium, owing to their large atomic sizes and high coordination spheres.

Sterically bulky ligands or neutral ligands, such as tetraethylene glycol dimethyl ethereal (tetraglyme), tetramethylethylenediamine (TMEDA), β -diketonates, and cyclopentadienyl groups, have been used to address these challenges and synthesize group two metal precursors with saturated metal centers.^{20–23} β -diketonates have been used to synthesize group two β -diketonate complexes with high volatility, such as Mg(tmhd)₂, Ca(tmhd)₂, Sr(tmhd)₂, [Sr(tmhd)₂(triglyme)], and $Ba(tmhd)_2$.²⁴⁻³¹ (tmhd = 2,2,6,6-tetramethyl-3,5-heptanedione, triglyme = $Me(OCH_2CH_2)_3OMe)$. A previous study observed the tendency of the strontium molecular structure using ethereal ligands with a varying number of oxygen atoms and varying β -diketonate ligands, such as tmhd, acac, tfac, and hfac. When hfacH was used, the hydroxyl hydrogen atom of the ethereal ligand with three or four oxygen atoms was substituted by trimethylsilyl from HMDS and showed high volatility.³² In this study, ethereal ligands and hfacH were applied to observe alcohol silvlation and to synthesize volatile complexes of other two group metals, such as magnesium,

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Scheme 1. Synthetic Scheme Complexes 1 and 2



Scheme 2. Synthetic Scheme Complexes 3 and 4



Scheme 3. Synthetic Scheme Complex 5



calcium, and barium. $Mg(dts)(hfac)_2$ (1), $Ca(dts)(hfac)_2$ (2), $Mg(dmts)(hfac)_2$ (3), $Ca(dmts)(hfac)_2$ (4), and $Ba(dmts)(hfac)_2$ (5) were synthesized by controlled substitution reactions using metal bis(bis(trimethylsilyl amide). In these complexes, compounds 2, 4, and 5 were characterized by using X-ray crystallography, and all compounds displayed monomeric structures. DFT calculations were conducted to investigate the alcohol silylation of these complexes, using complex 4 as a reference. The energy differences between each reaction intermediate were calculated to determine the key intermediate in silylation and propose a plausible reaction mechanism for this process. Chart 1 shows chemical structures of general ligands for synthesizing volatile metal precursor.

RESULTS AND DISCUSSION

In this study, new group two metal complexes were synthesized by in situ substitution reactions (Schemes 13). Complexes 2, 4, and 5 were recrystallized as a white solid from a saturated toluene solution at -30 °C. All complexes exhibited moderate yields of 70-80%. In our previous work, volatile strontium complexes with ethereal ligands have been shown to exhibit various strontium compound tendencies, which are affected by the steric hindrance, electron density, and coordination number of the central metal. When hfacH was added to strontium complexes, the hydrogen atom of ROH was substituted by trimethylsilyl from HMDS; the resulting compound exhibited highly volatile properties.

Therefore, further work was conducted to develop two group metal precursors with improved properties. Group two metal complexes were synthesized using ethereal and hfacH ligands to observe alcohol silvlation and investigate their thermal properties as precursors. Similar to strontium complexes Sr(dmts)(hfac)₂, other group two metals (magnesium, calcium, and barium) exhibited alcohol silvlation from ethereal ligands. In particular, complexes 4 and 5 were sublimed at 100 and 110 °C (1 Torr), whereas complex 1 was distilled at 110 °C (1 Torr). The NMR spectra of the respective complexes were recorded using C6D6 as the solvent and a standard at room temperature. In all complexes, the -OH peak was absent; however, the trimethylsilyl peak was observed because of the trimethylsylation of alcohol with HMDS. The CH₃ protons of mee and tmge for complexes 1, 2, 3, 4, and 5 were observed at $\delta_{\rm H}$ values of 3.02, 2.96, 2.96, 3.10, and 2.97 ppm, respectively. The β -CH protons of the hfac ligand for compounds 1, 2, 3, 4, and 5 were observed as singlets at $\delta_{
m H}$ values of 6.20, 6.28, 6.23, 6.31, and 6.29 ppm, respectively. The ¹⁹F NMR signals of $-2(CF_3)$ for compounds 1, 2, 3, 4, and 5 were observed at -77.38, -76.89, -76.71, -76.70, and -78.55 ppm, respectively.

FT-IR Spectra. The –OH stretching middle peaks of all complexes were absent in the FT-IR spectra; however, weak peaks were observed at $\nu = 2957 \text{ cm}^{-1}$ (1), 2951 cm⁻¹(2), 2943 cm⁻¹ (3), 2941 cm⁻¹ (4), and 2940 cm⁻¹ (5) (C–H stretching vibration); additionally, middle peaks were observed at $\nu = 1251 \text{ cm}^{-1}$ (1), 1249 cm⁻¹(2), 1249 cm⁻¹ (3), 1248 cm⁻¹ (4), and 1250 cm⁻¹ (5) (Si–CH₃ stretching vibration). This indicates that the trimethylsilylation of alcohol proceeded successfully in all compounds.

The FT-IR spectra exhibited C=O stretching peaks in coordinated β -diketones at 1654 cm⁻¹ (1), 1652 cm⁻¹(2), 1651 cm⁻¹ (3), 1656 cm⁻¹ (4), and 1651 cm⁻¹ (5), indicating that the reaction proceeded successfully.

Crystal Structure. X-ray-quality crystals of complexes 2, 4, and 5 were obtained from saturated toluene solutions at -30 °C. Complexes 2, 4, and 5 crystallized in monoclinic and triclinic space groups, where the silyl ether ligands exhibited a 5-membered ring structure (Figures 1, 2, and 3). All complexes exhibited a monomeric structure, where calcium and barium ions were bonded to two hfac ligands and coordinated to one



Figure 1. Crystal structure of $Ca(dts)(hfac)_2$ (2). Thermal ellipsoids are drawn at the 30% probability level and selected bond lengths (Å) and bond angles are represented in Table S2.



Figure 2. Crystal structure of $Ca(dmts)(hfac)_2$ (4). Thermal ellipsoids are drawn at the 30% probability level and selected bond lengths (Å) and bond angles are represented in Table S2.



Figure 3. Crystal structure of $Ba(dmts)(hfac)_2$ (5). Thermal ellipsoids are drawn at the 30% probability level and selected bond lengths (Å) and bond angles are represented in Table S2.

silyl ether ligand, resulting in alcohol silylation from HMDS and meeH or tmgeH ligands. The metal-to-oxygen bonding distance of complex 4 was longer than that of complex 2, which might be a result of high steric hindrance due to the presence of eight-coordinated oxygen atoms (Figure 2). The average O-M-O chelate angles of 3, 4, and 5 between the metal and mee or tmge ligands were 68.67° , 66.08° , and 59.06° , respectively (Figure 3). A gradual increase in bond angles between the metal and two hfac ligands was observed in the calcium (4), strontium, and barium (5) complexes (83.04, 86.77, and 88.90° , respectively).

DFT Calculation. The trimethylsilyl group shift was further investigated by DFT calculations using complex 4 as a representative model. The deprotonation and chelation of the tmgeH ligand and hfac ligands by chelated btsa ligands were highly exothermic processes ($\Delta G = -86.54$, $\Delta G = -112.01$, and -45.46 kcal/mol), as shown in Figure 4. During these processes, the deprotonated alcohol moiety in complexes 4a and 4b has the potential to react with HMDS via the S_N2 reaction pathway. However, a previous study using X-ray structural analysis showed that this moiety does not react with



Figure 4. Proposed mechanism for the silvlation of complex 4.

HMDS.³² After the formation of complex 4c, it was hypothesized that the reaction would proceed via a stepwise pathway. However, the energy difference between HMDS and complex 4c of the acid—base reaction was large owing to the nonpolar solvent condition ($\Delta G = 66.62$ kcal/mol). In contrast, the concerted reaction pathway proceeds with minimally charged intermediates in nonpolar solvents. This DFT study shows that the concerted reaction pathway may have a relatively low activation barrier with a minimal energy difference between the reactant and product ($\Delta G^{\ddagger} = 22.58$ kcal/mol and $\Delta G = -2.33$ kcal/mol). The driving force for this reaction was likely the electronegativity of the oxygen atom, which was higher than that of the nitrogen atom.³³

TGA. Thermogravimetric analysis (TGA) of complexes 1-5 was conducted from room temperature to 600 °C under a constant flow of nitrogen to prevent air contact (Figure 5). A three-step mass-loss pattern was observed in the TGA curves of complexes 3 and 5. In the first step (between 30 to 250 °C), TGA plots of complexes 3 and 5 exhibited 70 and 64% mass losses, respectively. During the other steps (between 250 and 500 °C), both complexes exhibited 21% and 20%, and residual masses of 9% and 16%, respectively; these values were similar to the mass percentages of MgO (5.93%) and BaO (19.4%). Complexes 1, 3, and 4 exhibited relatively sharp TGA curves between 35 and 228 °C; these complexes exhibited single-step weight losses of 99%, 97%, and 97.76% and residual masses of 1%, 2%, and 2%, respectively. Regarding magnesium,



Figure 5. TGA plot of complexes 1 (black), 2 (red), 3 (blue), 4 (green), and 5 (purple).

complexes with mee ligand were more volatile than compounds with tmge ligand, whereas calcium complexes with tmge ligand tended to be more volatile than calcium complex with mee ligand. These differences likely occurred because of the difference in the coordination number between the elements, which is based on the atomic size. Theses complexes with high volatility can be used as ALD or CVD precursors to fabricate metal oxide thin films.

Novel group two β -diketonate complexes with ethereal or silvl groups were synthesized and characterized. All complexes were prepared via a controlled substitution reaction with Mg(btsa)₂. DME, $Ca(btsa)_2$ ·DME, and $Ba(btsa)_2$ ·2DME. Compounds 2, 4, and 5 exhibited monomeric structures with hepta- or octacoordination states. In all complexes, the hydroxyl hydrogen of tmgeH and meeH was replaced by a trimethylsilyl group from HMDS as a byproduct. Si-CH₃ stretching vibration peaks were observed in the FT-IR spectra of all complexes. The TGA curves for complexes 1, 2, and 5 exhibited minimal nonvolatile residues and single-step weight losses. Using the DFT calculations of complex 4, a possible reaction pathway for silvlation was proposed based on the energy differences between each reaction intermediate. A concerted reaction pathway was favored because of the use of a nonpolar solvent; additionally, the difference in electronegativity between the oxygen and nitrogen atoms likely facilitated silylation.

EXPERIMENTAL SECTION

General Remarks. NMR spectra were recorded with a Bruker 500 MHz spectrometer (¹H, ¹³C, and ¹⁹F) with C_6D_6 as the solvent and reference. IR spectra were obtained using a Nicolet Nexus FT-IR spectrophotometer. Elemental analyses were carried out using a Thermo Scientific OEA Flash 2000 Analyzer. Thermogravimetric analyses were conducted using a SETARAM 92–18 TG-DTA instruments with a constant flow of nitrogen (500 mL/min) throughout the experiment. All reactions were carried out under inert dry conditions in an argon-filled glovebox. Hexane and toluene were purified using an Innovative Technology PS-MD-4 solvent purification system. All other chemicals were purchased from Aldrich and Alfa Aesar without further purification. $M[N(SiMe_3)]_2 \cdot 2L$ (*M*

= Mg, Ca, and Ba, L = DME) was prepared following previously reported methods.³⁴ Melting points were measured by the StuartTM SMP40 automatic melting point apparatus.

General Procedure for the Synthesis of Mg(dts)-(hfac)₂ and Ca(dts)(hfac)₂. A hexane solution (10 mL) of meeH (1 equiv) and hfacH (2 equiv) was added dropwise to a solution of $Mg(btsa)_2$ ·DME or Ca(btsa)₂·DME (1 equiv) in hexane (20 mL) at room temperature with constant stirring and stirred for 15 h. After the completion of the reaction, the reaction mixture was filtered and volatiles were removed in vacuo to obtain the product as a white solid. X-ray-quality crystals were grown from a saturated solution in toluene upon cooling.

Mg(dts)(hfac)₂ (1). Yield: 0.59 g (80%), ¹H NMR (500 MHz, C_6D_6): $\delta = 0.03$ [s, 9H], 3.02 [s, 3H], 3.04 [t, 2H], 3.43 [t, 2H], 3.46–3.48 [m, 4H], 6.20 [s, 2H, β –CH (hfac)] ppm. ¹³C NMR (125 MHz, C_6D_6): $\delta = -0.91$, 59.07, 61.76, 70.01, 70.97, 73.38, 90.36, 117.14, 179.59 ppm. ¹⁹F NMR (470.54 MHz, C_6D_6): $\delta = -77.38$ ppm. FT-IR (ATR, cm⁻¹): 2957(w), 1654(m), 1512(m), 1472(w), 1251(m), 1196(m), 1138(s), 1059 (m), 951(m), 842 (m), 663 (m), 584 (w). C₁₈H₂₂O₇Ca₁Si₁F₁₂(630.73): C, 34.28; H, 3.52. Found: C, 34.71; H, 3.53.

Ca(dts)(hfac)₂ (2). Yield: 0.53 g (80%), mp 70 °C. ¹H NMR (500 MHz, C₆D₆): δ = 0.06 [s, 9H], 2.82 [s, 4H], 2.91 [m, 4H], 2.96 [s, 3H], 2.97 [t, 2H], 3.11 [s, 6H], 3.14 [t, 2H], 6.28 [s, 2H, β -CH (hfac)] ppm. ¹³C NMR (125 MHz, C₆D₆): δ = -1.65, 58.88, 58.90, 61.80, 69.36, 70.55, 70.69, 71.63, 89.05, 117.56, 177.14 ppm. ¹⁹F NMR (470.54 MHz, C₆D₆): δ = -76.89 ppm. FT-IR (ATR, cm⁻¹): 2951(w), 1652(m), 1524(m), 1469(w), 1249(m), 1185(m), 1131(s), 1047(m), 8 4 2 (m), 7 9 3 (m), 6 5 9 (m), 5 2 6 (w). C₁₈H₂₂O₇Ca₁Si₁F₁₂(646.52): C, 33.44; H, 3.43. Found: C, 33.45; H, 3.19.

General Procedure for the Synthesis of Mg(dmts)-(hfac)₂, Ca(dmts)(hfac)₂, and Ba(dmts)(hfac)₂. A hexane solution (10 mL) of tmgeH (1 equiv) and hfacH (2 equiv) was added dropwise to a solution of Mg(btsa)₂·DME or Ca(btsa)₂. DME or Ba(btsa)₂·2DME (1 equiv) in hexane (20 mL) at room temperature with constant stirring and was stirred for 15 h. After the completion of the reaction, the reaction mixture was filtered and volatiles were removed in vacuo to obtain the product as white solid. X-ray-quality crystals were grown from a saturated solution in toluene upon cooling.

Mg(dmts)(hfac)₂ (3). Yield: 0.50 g (75%). ¹H NMR (500 MHz, C₆D₆): δ = 0.06 [s, 9H], 2.96 [s, 3H], 3.01 [t, br, 2H], 3.34 [t, 4H], 3.45 [t, 2H], 3.48 [m, br, 4H], 6.23 [s, 2H] ppm. ¹³C NMR (125 MHz, C₆D₆): δ = -0.61, 58.96, 61.97, 70.28, 70.54, 71.20, 72.97, 90.46, 116.81, 179.53 ppm. ¹⁹F NMR (470.54 MHz, C₆D₆): δ = -76.71 ppm. FT-IR (ATR, cm⁻¹): 2943(w), 1738(w), 1651(m), 1509(s), 1471(m), 1249(m), 1186(m), 1130(s), 1076(m), 956(m), 848(s), 754(w), 575(m). C₂₀H₂₆O₈Ca₁Si₁F₁₂(674.52): C, 35.60; H, 3.88. Found: C, 35.27; H, 3.48.

Ca(dmts)(hfac)₂ (4). Yield: 0.59 g (80%), mp 100 °C. ¹H NMR (500 MHz, C₆D₆): δ = 0.04 [s, 9H], 2.67 [t, 2H], 2.84 [t, 2H], 3.08 [t, 2H], 3.10 [s, 3H], 3.14 [t, 2H], 3.22 [s, 2H], 3.27 [s, 2H], 6.31 [s, 2H, β -CH (hfac)] ppm. ¹³C NMR (125 MHz, C₆D₆): δ = -1.50, 59.80, 62.24, 68.31, 69.73, 70.12, 71.11, 88.49, 119.96, 176.77 ppm. ¹⁹F NMR (470.54 MHz, C₆D₆): δ = -76.70 ppm. FT-IR (ATR, cm⁻¹): 2941(w), 1656(m), 1516(m), 1495(w), 1248(m), 1178(m), 1136(s), 1075(m), 948(m), 846(m), 658(m), 578(w). $C_{20}H_{26}O_8Ca_1Si_1F_{12}(690.58){\rm :}$ C, 34.79; H, 3.79. Found: C, 33.31; H, 3.24.

Ba(dmts)(hfac)₂ (**5**). Yield: 0.61 g (78%), mp 110 °C. ¹H NMR (500 MHz, C_6D_6): $\delta = 0.03$ [s, 9H], 2.80 [t, 2H], 2.93 [t, 2H], 2.97 [s, 3H], 3.03 [t, 2H], 3.08 [t, 2H], 3.25[t, 2H], 6.29 [s, 2H] ppm. ¹³C NMR (125 MHz, C_6D_6): $\delta = -1.67$, 58.66, 62.17, 69.77, 70.07, 70.95, 72.46, 88.07, 117.46, 175.83 ppm. ¹⁹F NMR (470.54 MHz, C_6D_6): $\delta = -78.55$ ppm. FT-IR (ATR, cm⁻¹): 2940(m), 1738(m), 1651(m), 1524(m), 1509(m), 1250(m), 1130(s), 1076(s), 956(w), 848(m), 790(m), 754(w), 693(m). $C_{20}H_{26}O_8Ba_1Si_1F_{12}(787.84)$: C, 30.49; H, 3.33. Found: C, 30.52; H, 3.28.

Computational Details. The geometries were calculated in Orca 5.02 software³⁵ using the B3LYP functional.^{36–39} Optimization and frequency calculation were proceeded using the def2-SVP basis set⁴⁰ with the auxiliary def2/J basis set⁴¹ was used for all atoms. The single-point energy of optimized geometries was calculated using the def2-TZVPP basis set⁴⁰ with the auxiliary def2/J basis set⁴¹ for all atoms. Each structure was confirmed by frequency calculations at the same level of theory to be a real local minimum on the potential energy surface. Solvation-free energies in hexane were calculated by using the polarizable continuum model (C-PCM) using Bondi atomic radii.^{42–44}

ASSOCIATED CONTENT

Supporting Information

The Supporting Information is available free of charge at https://pubs.acs.org/doi/10.1021/acsomega.4c03479.

Crystallographic information for Complex 2(CIF)

Crystallographic information for Complex 3(CIF)

Crystallographic information for Complex 4(CIF)

The crystallographic data and data collection parameters selected bond lengths (Å) and bond angle (deg) for complexes 2, 4, 5 (Tables S1 and 2). ¹H NMR, ¹³C NMR, and¹⁹F-NMR spectrum of all Complexes (Figure S1–15). Optimized transition state structure for silylation of Complex 4 (Figure S16). Cartesian coordinates of all optimized structures (PDF)

AUTHOR INFORMATION

Corresponding Author

Taek-Mo Chung – Thin Film Materials Research Center, Korea Research Institute of Chemical Technology, Daejeon 34114, Republic of Korea; Department of Chemical Convergence Materials, University of Science and Technology (UST), Daejeon 34113, Republic of Korea; Orcid.org/ 0000-0002-5169-2671; Email: tmchung@krict.re.kr

Authors

- **Chanwoo Park** Thin Film Materials Research Center, Korea Research Institute of Chemical Technology, Daejeon 34114, Republic of Korea; Department of Chemistry, Korea University, Seoul 02841, Republic of Korea
- Seungjin Song Thin Film Materials Research Center, Korea Research Institute of Chemical Technology, Daejeon 34114, Republic of Korea
- Heenang Choi Thin Film Materials Research Center, Korea Research Institute of Chemical Technology, Daejeon 34114, Republic of Korea; Department of Chemistry, Sungkyunkwan University (SKKU), Gyeonggi-do 16419, Republic of Korea

- Bo Keun Park Thin Film Materials Research Center, Korea Research Institute of Chemical Technology, Daejeon 34114, Republic of Korea; Department of Chemical Convergence Materials, University of Science and Technology (UST), Daejeon 34113, Republic of Korea; Orcid.org/0000-0002-4066-0500
- Ji Yeon Ryu Thin Film Materials Research Center, Korea Research Institute of Chemical Technology, Daejeon 34114, Republic of Korea; orcid.org/0000-0001-6321-5576
- Youngkwon Kim Thin Film Materials Research Center, Korea Research Institute of Chemical Technology, Daejeon 34114, Republic of Korea; orcid.org/0000-0002-5788-8026

Complete contact information is available at: https://pubs.acs.org/10.1021/acsomega.4c03479

Author Contributions

[#]C.P., S.S. contributed equally.

Notes

The authors declare no competing financial interest.

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